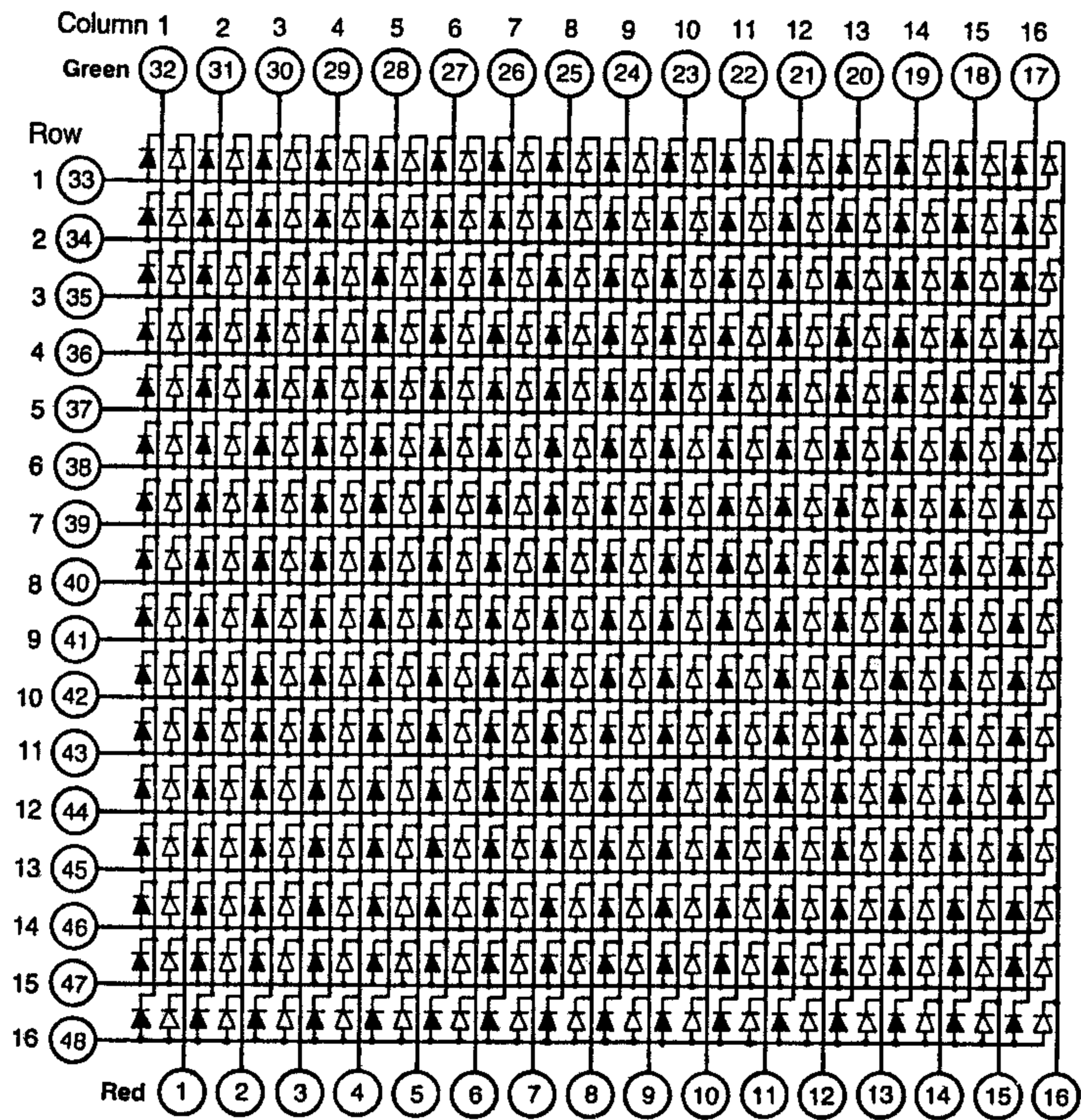
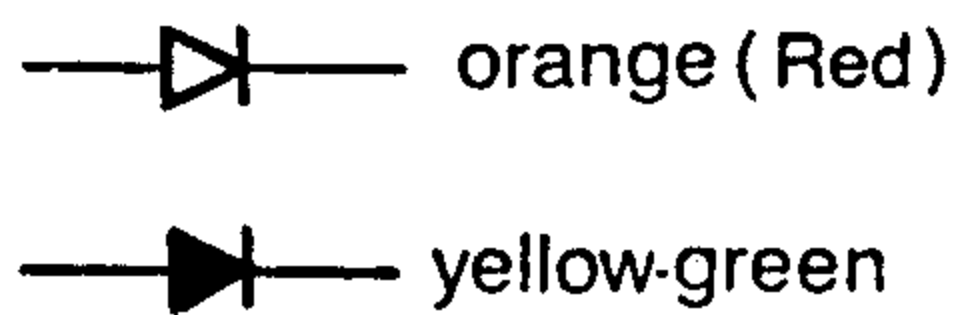
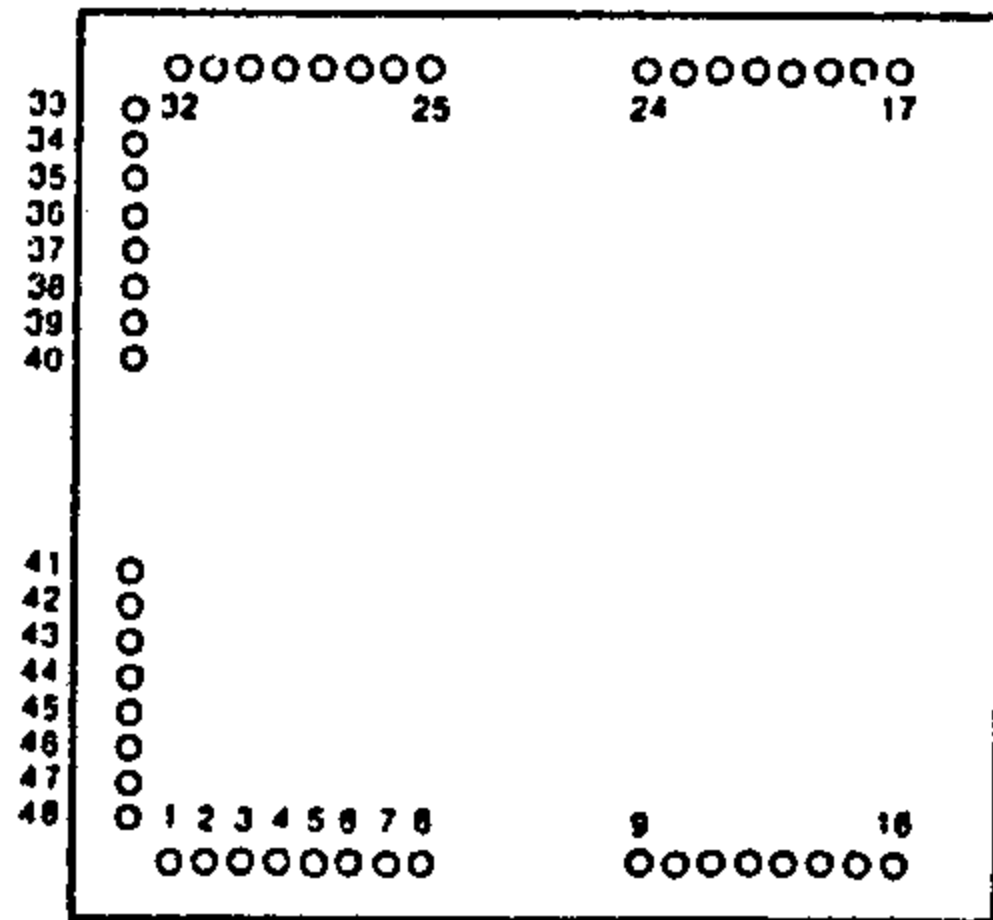


PIN ARRANGEMENT (Top View)



SDM 3169 SR-UG (GaAsP/GaP-GaP)

Orange SR SIDE (GaAsP/GaP) GaP)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Power dissipation/Total	2500	mW
Power dissipation/Chip	20	mW
Forward current	10	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	-25 ~ +85	$^\circ\text{C}$
Storage temperature	-55 ~ +100	$^\circ\text{C}$

Electrical/Optical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V_F	$I_F = 10\text{mA}$	—	2.0	2.2	V
Reverse current/Chip	I_R	$V_R = 4\text{V}$	—	—	10	μA
Luminous Intensity/Chip	I_v	$I_F = 10\text{mA}$	500	1000	—	μcd
Peak wavelength	λ_P	$I_F = 10\text{mA}$	—	635	—	nm
Spectral line halfwidth	$\Delta\lambda$	$I_F = 10\text{mA}$	—	35	—	nm

Yellow-green UG SIDE (GaP)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Power dissipation/Total	2500	mW
Power dissipation/Chip	20	mW
Forward current	10	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	-25 ~ +85	$^\circ\text{C}$
Storage temperature	-55 ~ +100	$^\circ\text{C}$

Electrical/Optical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V_F	$I_F = 10\text{mA}$	—	2.1	2.3	V
Reverse current/Chip	I_R	$V_R = 4\text{V}$	—	—	10	μA
Luminous intensity/Chip	I_v	$I_F = 10\text{mA}$	600	1200	—	μcd
Peak wavelength	λ_P	$I_F = 10\text{mA}$	—	565	—	nm
Spectral line halfwidth	$\Delta\lambda$	$I_F = 10\text{mA}$	—	30	—	nm

* Duty ratio=1/16, Pulse width=0.1ms, Lighting ratio=50%